

Fig 1. X-ray diffraction of a bilayer sample of GaN/ZrN deposited on Si/3C-SiC (001)

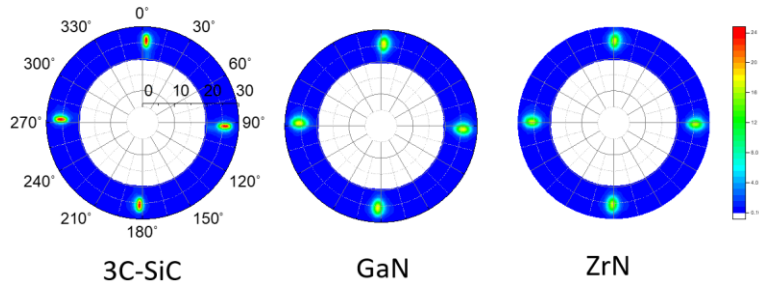


Fig 2. Pole figures around the (113) peak of each epitaxial layer above the Si substrate in a superlattice sample of GaN and ZrN

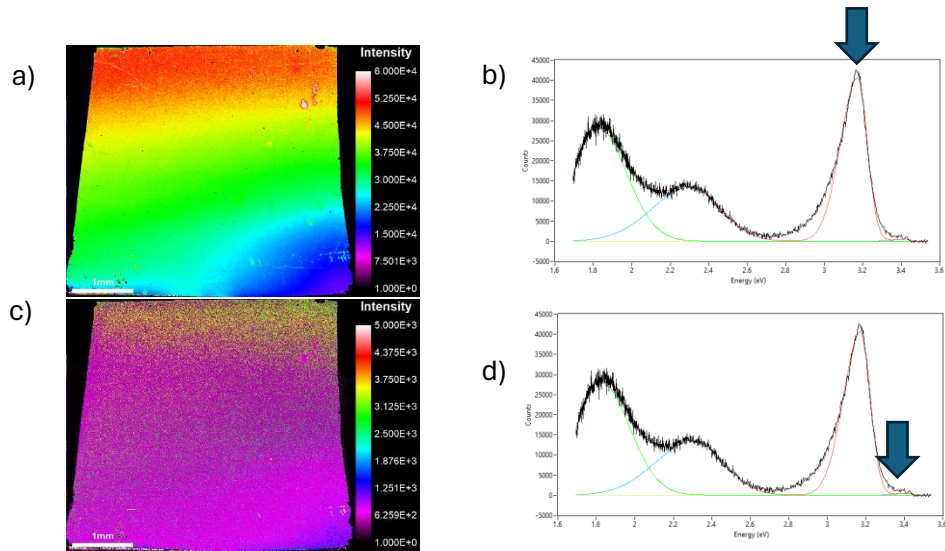


Fig 3. Photoluminescence of the cubic (a, b) and hexagonal (c, d) band gaps of GaN in a representative sample